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Berg, A.; Yazdi, Sadegh; Nowzari, A.; Storm, K.; Wagner, Jakob Birkedal; Jain, V.; Vainorius, N.

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Radial nanowire light-emitting diodes in the \((\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}\) material system

A. Berg,¹ S. Yazdi,² ³ A. Nowzari,¹ K. Storm,¹ V. Jain,¹ ⁴ N. Vainorius,¹ L. Samuelson,¹ J. B. Wagner² and M. T. Borgström¹

¹ Solid State Physics, Lund University, Box 118, SE-221 00, Lund, Sweden
² Center for Electron Nanoscopy, Technical University of Denmark, DK 2800 Kgs. Lyngby, Denmark
³ Department of Materials Science and NanoEngineering, Rice University, 6100 Main Street MS-325, Houston, TX 77005, United States
⁴ Laboratory of Mathematics, Physics and Electrical Engineering, Halmstad University, Box 823, SE-301 18 Halmstad, Sweden

We present a growth scheme for radial nanowire (NW) quantum-well pin-junction structures in the AlGaInP material system. The different layers were analyzed by XRD with respect to lattice-matching and the structural properties evaluated by STEM-EDX. We find Al segregation in the corners of the AlGaInP shells and Ga enrichment in the corners of the GaInP layers. After vertical NW processing, we measured the electro-optical properties of the NWs and the LED devices illuminated with red color at a forward bias of about 3 V.

Radial nanowires could play an important role for next-generation light-emitting diodes because the NW core can be used as a “substrate” and shells can be grown with the desired optical wavelength. Here, we use the AlGaInP material system which is suitable for long-wavelength visible emission. Ternary GaInP acts as active layer for light emission and AlGaInP as charge carrier barriers.

By use of metal-organic chemical vapor deposition (MOCVD), the p-type GaInP NW core was grown with homogeneous material composition from a regular pattern defined by nanoimprint lithography [¹]. Several shells were grown lattice-matched to the NW core with composition leading to red luminescence.

STEM-EDX measurements show Al enrichment in the corners and we conclude that Al tends to segregate towards the vertices of the hexagon. Electrical injection luminescence (IL) measurements show a peak at around 1.85 eV while the peak does not shift with increasing current [²].

![Al-K, Ga-K, In-L, P-K maps](image1)

![IL measurements](image2)

Fig. 1. Left: Al, Ga, In and P maps measured using STEM-EDX elemental mapping on GaInP/AlGaInP/GaInP core-shell NWs. Right: IL measurements with different currents.

References
